

Noritaka Usami

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

513
papers

8,133
citations

42
h-index

69
g-index

589
ext. papers

9,050
ext. citations

2.4
avg, IF

5.9
L-index

#	Paper	IF	Citations
513	ZnGeO Passivating Interlayers for BaSi Thin-Film Solar Cells.. <i>ACS Applied Materials & Interfaces</i> , 2022 ,	9.5	1
512	Fabrication of BaSi ₂ homojunction diodes on Nb-doped TiO ₂ coated glass substrates by aluminum-induced crystallization and two-step evaporation method. <i>Japanese Journal of Applied Physics</i> , 2022 , 61, SC1029	1.4	2
511	Data-Driven Optimization and Experimental Validation for the Lab-Scale Mono-Like Silicon Ingot Growth by Directional Solidification.. <i>ACS Omega</i> , 2022 , 7, 6665-6673	3.9	2
510	Improved conversion efficiency of p-type BaSi ₂ /n-type crystalline Si heterojunction solar cells by a low growth rate deposition of BaSi ₂ . <i>AIP Advances</i> , 2022 , 12, 045115	1.5	0
509	Origin of recombination activity of non-coherent B{111} grain boundaries with a positive deviation in the tilt angle in cast-grown silicon ingots. <i>Applied Physics Express</i> , 2021 , 14, 011002	2.4	4
508	Mechanisms of carrier lifetime enhancement and conductivity-type switching on hydrogen-incorporated arsenic-doped BaSi ₂ . <i>Thin Solid Films</i> , 2021 , 724, 138629	2.2	5
507	Occurrence Prediction of Dislocation Regions in Photoluminescence Image of Multicrystalline Silicon Wafers Using Transfer Learning of Convolutional Neural Network. <i>IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences</i> , 2021 , E104.A, 857-865	0.4	1
506	Activation energy of hydrogen desorption from high-performance titanium oxide carrier-selective contacts with silicon oxide interlayers. <i>Current Applied Physics</i> , 2021 , 21, 36-42	2.6	9
505	Propagation of Crystal Defects during Directional Solidification of Silicon via Induction of Functional Defects. <i>Crystals</i> , 2021 , 11, 90	2.3	2
504	Passivation mechanism of the high-performance titanium oxide carrier-selective contacts on crystalline silicon studied by spectroscopic ellipsometry. <i>Japanese Journal of Applied Physics</i> , 2021 , 60, SBBF04	1.4	2
503	Simulation study on lateral minority carrier transport in the surface inversion layer of the p-aSi:H/i-aSi:H/cSi heterojunction solar cell. <i>Japanese Journal of Applied Physics</i> , 2021 , 60, 026503	1.4	1
502	Fabrication of Silicon Nanowire Metal-Oxide-Semiconductor Capacitors with Al ₂ O ₃ /TiO ₂ /Al ₂ O ₃ Stacked Dielectric Films for the Application to Energy Storage Devices. <i>Energies</i> , 2021 , 14, 4538	3.1	2
501	Direct prediction of electrical properties of grain boundaries from photoluminescence profiles using machine learning. <i>Applied Physics Letters</i> , 2021 , 119, 032105	3.4	0
500	Improved Performance of Titanium Oxide/Silicon Oxide Electron-Selective Contacts by Implementation of Magnesium Interlayers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021 , 218, 2100296	1.6	0
499	Contact control of Al/Si interface of Si solar cells by local contact opening method. <i>Materials Chemistry and Physics</i> , 2021 , 270, 124833	4.4	
498	Application of Bayesian optimization for high-performance TiO _x /SiO _y /c-Si passivating contact. <i>Solar Energy Materials and Solar Cells</i> , 2021 , 230, 111251	6.4	3
497	Fabrication of heterojunction crystalline Si solar cells with BaSi ₂ thin films prepared by a two-step evaporation method. <i>Japanese Journal of Applied Physics</i> , 2021 , 60, 105503	1.4	6

496	Impact of chemically grown silicon oxide interlayers on the hydrogen distribution at hydrogenated amorphous silicon/crystalline silicon heterointerfaces. <i>Applied Surface Science</i> , 2021 , 567, 150799	6.7	1
495	Versatile fabrication of a passivation material, solute PEDOT:PSS, for a c-Si substrate using alcoholic solvents. <i>Sustainable Energy and Fuels</i> , 2021 , 5, 666-670	5.8	
494	Application of Bayesian optimization for improved passivation performance in TiO _x /SiO _y /c-Si heterostructure by hydrogen plasma treatment. <i>Applied Physics Express</i> , 2021 , 14, 025503	2.4	5
493	Influence of the time-dependent vapor composition on structural properties of the BaSi ₂ thin films fabricated by vacuum evaporation. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SFFA10	1.4	8
492	Impact of Ge deposition temperature on parameters of c-Si solar cells with surface texture formed by etching of Si using SiGe islands as a mask. <i>Materials Science in Semiconductor Processing</i> , 2020 , 114, 105065	4.3	3
491	Drastic enhancement of photoresponsivity in C-doped BaSi ₂ films formed by radio-frequency sputtering. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SFFA06	1.4	4
490	Effects of evaporation vapor composition and post-annealing conditions on carrier density of undoped BaSi ₂ evaporated films. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SFFA05	1.4	7
489	Impact of deposition of indium tin oxide double layers on hydrogenated amorphous silicon/crystalline silicon heterojunction. <i>AIP Advances</i> , 2020 , 10, 065008	1.5	2
488	Significant enhancement of photoresponsivity in As-doped n-BaSi ₂ epitaxial films by atomic hydrogen passivation. <i>Applied Physics Express</i> , 2020 , 13, 051001	2.4	5
487	Atomic hydrogen passivation for photoresponsivity enhancement of boron-doped p-BaSi ₂ films and performance improvement of boron-doped p-BaSi ₂ /n-Si heterojunction solar cells. <i>Journal of Applied Physics</i> , 2020 , 127, 233104	2.5	8
486	Effect of forming gas annealing on hydrogen content and surface morphology of titanium oxide coated crystalline silicon heterocontacts. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020 , 38, 022415	2.9	3
485	Scalable fabrication of GaN on amorphous substrates via MOCVD on highly oriented silicon seed layers. <i>Journal of Crystal Growth</i> , 2020 , 535, 125522	1.6	1
484	Point defects in BaSi ₂ thin films for photovoltaic applications studied by positron annihilation spectroscopy. <i>Journal of Applied Physics</i> , 2020 , 127, 085304	2.5	6
483	Effect of hydrogen plasma treatment on the passivation performance of TiO _x on crystalline silicon prepared by atomic layer deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020 , 38, 022410	2.9	9
482	Synthesis of Mg ₂ Si thin film by thermal treatment under inert gas atmosphere and evaluation of film quality. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SFFB03	1.4	
481	Preparation and thermoelectric characterization of phosphorus-doped Si nanocrystals/silicon oxide multilayers. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SGGF09	1.4	0
480	Fabrication of group IV semiconductor alloys on Si substrate applying Al paste with screen-printing. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SGGF07	1.4	
479	3D visualization of growth interfaces in cast Si ingot using inclusions distribution. <i>Journal of Crystal Growth</i> , 2020 , 535, 125535	1.6	

478	Undoped p-type BaSi ₂ emitter prepared by thermal evaporation and post-annealing for crystalline silicon heterojunction solar cells. <i>Applied Physics Express</i> , 2020 , 13, 051002	2.4	7
477	Effect of the Niobium-Doped Titanium Oxide Thickness and Thermal Oxide Layer for Silicon Quantum Dot Solar Cells as a Dopant-Blocking Layer. <i>Nanoscale Research Letters</i> , 2020 , 15, 39	5	1
476	Surface inversion layer effective minority carrier mobility as one of the measures of surface quality of the p-aSi:H/i-aSi:H/cSi heterojunction solar cell. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SGGF06	1.4	1
475	Generation of dislocation clusters at triple junctions of random angle grain boundaries during cast growth of silicon ingots. <i>Applied Physics Express</i> , 2020 , 13, 105505	2.4	7
474	Surface-orientation control of silicon thin films via aluminum-induced crystallization on monocrystalline cubic substrates. <i>Journal of Crystal Growth</i> , 2020 , 533, 125441	1.6	2
473	The impact of highly excessive PbI ₂ on the correlation of MAPbI ₃ perovskite morphology and carrier lifetimes. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 14481-14489	7.1	6
472	Determination of carrier recombination velocity at inclined grain boundaries in multicrystalline silicon through photoluminescence imaging and carrier simulation. <i>Journal of Applied Physics</i> , 2020 , 128, 125103	2.5	3
471	Reactive deposition growth of highly (001)-oriented BaSi ₂ films by close-spaced evaporation. <i>Materials Science in Semiconductor Processing</i> , 2020 , 113, 105044	4.3	10
470	Effect of Si substrate modification on improving the crystalline quality, optical and electrical properties of thermally-evaporated BaSi ₂ thin-films for solar cell applications. <i>International Journal of Modern Physics B</i> , 2020 , 34, 2050068	1.1	1
469	Mössbauer spectroscopic microscope study on diffusion and segregation of Fe impurities in mc-Si wafer. <i>Hyperfine Interactions</i> , 2019 , 240, 1	0.8	1
468	Fine line Al printing on narrow point contact opening for front side metallization 2019 ,		7
467	Impact of size distributions of Ge islands as etching masks for anisotropic etching on formation of anti-reflection structures. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, 045505	1.4	8
466	Pole figure analysis from electron backscatter diffraction: An effective method of evaluating fiber-textured silicon thin films as seed layers for epitaxy. <i>Applied Physics Express</i> , 2019 , 12, 025501	2.4	1
465	Fabrication of Si _{1-x} Ge _x layer on Si substrate by Screen-Printing. <i>MRS Advances</i> , 2019 , 4, 749-754	0.7	2
464	Effects of Surface Doping of Si Absorbers on the Band Alignment and Electrical Performance of TiO ₂ -Based Electron-Selective Contacts. <i>MRS Advances</i> , 2019 , 4, 769-775	0.7	1
463	Evidence of solute PEDOT:PSS as an efficient passivation material for fabrication of hybrid c-Si solar cells. <i>Sustainable Energy and Fuels</i> , 2019 , 3, 1448-1454	5.8	10
462	Epitaxial growth of SiGe on Si substrate by printing and firing of Al/Ge mixed paste. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, 045504	1.4	1
461	3D visualization and analysis of dislocation clusters in multicrystalline silicon ingot by approach of data science. <i>Solar Energy Materials and Solar Cells</i> , 2019 , 189, 239-244	6.4	8

460	Hydrogen concentration at a-Si:H/c-Si heterointerfaces—the impact of deposition temperature on passivation performance. <i>AIP Advances</i> , 2019 , 9, 075115	1.5	14
459	Tuning the Electrical Properties of Titanium Oxide Bilayers Prepared by Atomic Layer Deposition at Different Temperatures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019 , 216, 1900495	1.6	3
458	Application of artificial neural network to optimize sensor positions for accurate monitoring: an example with thermocouples in a crystal growth furnace. <i>Applied Physics Express</i> , 2019 , 12, 125503	2.4	9
457	Marked enhancement of the photoresponsivity and minority-carrier lifetime of BaSi ₂ passivated with atomic hydrogen. <i>Physical Review Materials</i> , 2019 , 3,	3.2	15
456	Fabrication of Si _{1-x} Sn _x Layer on Si Substrate by Screen-Printing of Al-Sn Paste. <i>ECS Transactions</i> , 2019 , 93, 61-62	1	
455	Local Structure of High Performance TiO _x Electron-Selective Contact Revealed by Electron Energy Loss Spectroscopy. <i>Advanced Materials Interfaces</i> , 2019 , 6, 1801645	4.6	9
454	Alternative simple method to realize p-type BaSi ₂ thin films for Si heterojunction solar cell applications. <i>MRS Advances</i> , 2018 , 3, 1435-1442	0.7	11
453	Effect of substrate type on the electrical and structural properties of TiO ₂ thin films deposited by reactive DC sputtering. <i>Journal of Crystal Growth</i> , 2018 , 491, 120-125	1.6	6
452	Fabrication of silicon nanowire based solar cells using TiO ₂ /Al ₂ O ₃ stack thin films. <i>MRS Advances</i> , 2018 , 3, 1419-1426	0.7	2
451	A quantum-dot spin qubit with coherence limited by charge noise and fidelity higher than 99.9. <i>Nature Nanotechnology</i> , 2018 , 13, 102-106	28.7	340
450	BaSi ₂ formation mechanism in thermally evaporated films and its application to reducing oxygen impurity concentration. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 04FS01	1.4	13
449	Application of weighted Voronoi diagrams to analyze nucleation sites of multicrystalline silicon ingots. <i>Journal of Crystal Growth</i> , 2018 , 499, 62-66	1.6	4
448	Impact of boron incorporation on properties of silicon solar cells employing p-type polycrystalline silicon grown by aluminum-induced crystallization. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RB12	1.4	3
447	Investigation of effective near-infrared light-trapping structure with submicron diameter for crystalline silicon thin film solar cells. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RB21	1.4	1
446	Simple method for significant improvement of minority-carrier lifetime of evaporated BaSi ₂ thin film by sputtered-AlO _x passivation. <i>Materials Science in Semiconductor Processing</i> , 2018 , 76, 37-41	4.3	19
445	Fabrication and properties characterization of BaSi ₂ thin-films thermally-evaporated on Ge (100) modified substrates. <i>Thin Solid Films</i> , 2018 , 663, 14-20	2.2	2
444	Suppression of Near-interface Oxidation in Thermally-evaporated BaSi ₂ Films and Its Effects on Preferred Orientation and the Rectification Behavior of n-BaSi ₂ /p ⁺ -Si Diodes. <i>MRS Advances</i> , 2018 , 3, 1387-1392	0.7	5
443	Formation of light-trapping structure using Ge islands grown by gas-source molecular beam epitaxy as etching masks. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RB04	1.4	2

442	Formation of black silicon using SiGe self-assembled islands as a mask for selective anisotropic etching of silicon. <i>Materials Science in Semiconductor Processing</i> , 2018 , 75, 143-148	4.3	9
441	Influence of barrier layer height on the performance of Si quantum dot solar cells. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RF08	1.4	1
440	Fabrication of light-trapping structure by selective etching of thin Si substrates masked with a Ge dot layer and nanomasks. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RF09	1.4	3
439	Optimized electrical control of a Si/SiGe spin qubit in the presence of an induced frequency shift. <i>Npj Quantum Information</i> , 2018 , 4,	8.6	13
438	Controllable Optical and Electrical Properties of Nb Doped TiO ₂ Films by RF Sputtering 2018 ,		1
437	Improving the photoresponse spectra of BaSi ₂ layers by capping with hydrogenated amorphous Si layers prepared by radio-frequency hydrogen plasma. <i>AIP Advances</i> , 2018 , 8, 055306	1.5	7
436	Activation mechanism of TiO _x passivating layer on crystalline Si. <i>Applied Physics Express</i> , 2018 , 11, 1023014	2.4	10
435	Study on ion implantation conditions in fabricating compressively strained Si/relaxed Si _{1-x} C _x heterostructures using the defect control by ion implantation technique. <i>Journal of Crystal Growth</i> , 2017 , 468, 601-604	1.6	
434	Hole mobility in strained Si/SiGe/vicinal Si(110) grown by gas source MBE. <i>Journal of Crystal Growth</i> , 2017 , 468, 625-629	1.6	6
433	Controlling impurity distributions in crystalline Si for solar cells by using artificial designed defects. <i>Journal of Crystal Growth</i> , 2017 , 468, 610-613	1.6	7
432	Thermal stability of compressively strained Si/relaxed Si _{1-x} C _x heterostructures formed on Ar ion implanted Si (100) substrates. <i>Materials Science in Semiconductor Processing</i> , 2017 , 70, 127-132	4.3	
431	Exploring the potential of semiconducting BaSi ₂ for thin-film solar cell applications. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 023001	3	69
430	Investigation of p-type emitter layer materials for heterojunction barium disilicide thin film solar cells. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 05DB04	1.4	4
429	Effects of grain boundary structure controlled by artificially designed seeds on dislocation generation. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 075501	1.4	5
428	On the growth mechanism of multicrystalline silicon ingots with small grains fabricated using single-layer silicon beads. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 075502	1.4	5
427	Boron-doped p-BaSi ₂ /n-Si solar cells formed on textured n-Si(0 0 1) with a pyramid structure consisting of {1 1 1} facets. <i>Journal of Crystal Growth</i> , 2017 , 475, 186-191	1.6	6
426	Effect of ALD-Al ₂ O ₃ Passivated Silicon Quantum Dot Superlattices on p/i/n+ Solar Cells. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 2886-2892	2.9	4
425	Impact of anodic aluminum oxide fabrication and post-deposition anneal on the effective carrier lifetime of vertical silicon nanowires. <i>Solar Energy Materials and Solar Cells</i> , 2017 , 166, 39-44	6.4	2

4 ²⁴	Towards optimized nucleation control in multicrystalline silicon ingot for solar cells. <i>Journal of Crystal Growth</i> , 2017 , 468, 620-624	1.6	6
4 ²³	Development of spin-coated copper iodide on silicon for use in hole-selective contacts. <i>Energy Procedia</i> , 2017 , 124, 598-603	2.3	7
4 ²²	Controlling impurity distribution in quasi-mono crystalline Si ingot by seed manipulation for artificially controlled defects technique. <i>Energy Procedia</i> , 2017 , 124, 734-739	2.3	6
4 ²¹	Numerical simulation and performance optimization of perovskite solar cell 2017 ,		1
4 ²⁰	Growth of strained Si/relaxed SiGe heterostructures on Si(110) substrates using solid-source molecular beam epitaxy. <i>Semiconductor Science and Technology</i> , 2017 , 32, 114002	1.8	2
4 ¹⁹	Effects of surface morphology randomness on optical properties of Si-based photonic nanostructures. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 08MA02	1.4	1
4 ¹⁸	Formation of metastable cubic phase in SnS thin films fabricated by thermal evaporation. <i>Thin Solid Films</i> , 2017 , 639, 7-11	2.2	24
4 ¹⁷	Selective etching of Si, SiGe, Ge and its usage for increasing the efficiency of silicon solar cells. <i>Semiconductors</i> , 2017 , 51, 1542-1546	0.7	7
4 ¹⁶	Postannealing effects on undoped BaSi ₂ evaporated films grown on Si substrates. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 05DB05	1.4	16
4 ¹⁵	Minority-carrier lifetime and photoresponse properties of B-doped p-BaSi ₂ , a potential light absorber for solar cells. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 05DB01	1.4	5
4 ¹⁴	Fabrication of BaSi ₂ thin films capped with amorphous Si using a single evaporation source. <i>Thin Solid Films</i> , 2017 , 636, 546-551	2.2	7
4 ¹³	Optical characterization of double-side-textured silicon wafer based on photonic nanostructures for thin-wafer crystalline silicon solar cells. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 04CS01	1.4	0
4 ¹²	Growth of BaSi ₂ film on Ge(100) by vacuum evaporation and its photoresponse properties. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 05DB06	1.4	5
4 ¹¹	Post-annealing effects on the surface structure and carrier lifetime of evaporated BaSi ₂ films. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 04CS07	1.4	9
4 ¹⁰	Investigation on the origin of preferred a -axis orientation of BaSi ₂ films deposited on Si(100) by thermal evaporation. <i>Materials Science in Semiconductor Processing</i> , 2017 , 72, 93-98	4.3	10
4 ⁰⁹	Effect of grain boundary character of multicrystalline Si on external and internal (phosphorus) gettering of impurities. <i>Progress in Photovoltaics: Research and Applications</i> , 2016 , 24, 1615-1625	6.8	2
4 ⁰⁸	Photoresponse properties of BaSi ₂ film grown on Si (100) by vacuum evaporation. <i>Materials Research Express</i> , 2016 , 3, 076204	1.7	17
4 ⁰⁷	Growth direction control of dendrite crystals in parallel direction to realize high-quality multicrystalline silicon ingot. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 091302	1.4	2

406	Control of electrical properties of BaSi ₂ thin films by alkali-metal doping using alkali-metal fluorides. <i>Thin Solid Films</i> , 2016 , 603, 218-223	2.2	6
405	Simple Vacuum Evaporation Route to BaSi ₂ Thin Films for Solar Cell Applications. <i>Procedia Engineering</i> , 2016 , 141, 27-31		17
404	On the Mechanism of BaSi ₂ Thin Film Formation on Si Substrate by Vacuum Evaporation. <i>Procedia Engineering</i> , 2016 , 141, 23-26		19
403	Influence of surface roughness of ZnO layer on the growth of polycrystalline Si layer via aluminum-induced layer exchange process. <i>Journal of Advanced Marine Engineering and Technology</i> , 2016 , 40, 692-697	1.5	
402	Compressively strained Si/Si _{1-x} C _x heterostructures formed on Ar ion implanted Si(100) substrates. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 031302	1.4	3
401	Impact of silicon quantum dot super lattice and quantum well structure as intermediate layer on p-i-n silicon solar cells. <i>Progress in Photovoltaics: Research and Applications</i> , 2016 , 24, 774-780	6.8	15
400	Effects of deposition rate on the structure and electron density of evaporated BaSi ₂ films. <i>Journal of Applied Physics</i> , 2016 , 120, 045103	2.5	26
399	Novel light trapping structure by alkaline etching using a Ge dot mask for crystalline Si solar cells 2016 ,		2
398	Application of new doping techniques to solar cells for low temperature fabrication 2016 ,		1
397	p-BaSi ₂ /n-Si heterojunction solar cells with conversion efficiency reaching 9.0%. <i>Applied Physics Letters</i> , 2016 , 108, 152101	3.4	62
396	Improved multicrystalline silicon ingot quality using single layer silicon beads coated with silicon nitride as seed layer. <i>Journal of Crystal Growth</i> , 2016 , 441, 124-130	1.6	11
395	Effect of passivation layer grown by atomic layer deposition and sputtering processes on Si quantum dot superlattice to generate high photocurrent for high-efficiency solar cells. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 032303	1.4	8
394	Modulated surface nanostructures for enhanced light trapping and reduced surface reflection of crystalline silicon solar cells. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 052302	1.4	4
393	Effects of the Si/Al layer thickness on the continuity, crystalline orientation and the growth kinetics of the poly-Si thin films formed by aluminum-induced crystallization. <i>Thin Solid Films</i> , 2016 , 616, 213-219 ^{2.2}		16
392	Light-induced Recovery of Effective Carrier Lifetime in Boron-doped Czochralski Silicon at Room Temperature. <i>Energy Procedia</i> , 2016 , 92, 801-807	2.3	1
391	Evidence for efficient passivation of vertical silicon nanowires by anodic aluminum oxide. <i>Solar Energy Materials and Solar Cells</i> , 2016 , 157, 393-398	6.4	3
390	Cross-sectional potential profile across a BaSi ₂ p-n junction by Kelvin probe force microscopy. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 030306	1.4	3
389	Suppression of metastable-phase inclusion in N-polar (0001) InGa _{1-x} N/GaN multiple quantum wells grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2015 , 106, 222102	3.4	5

388	Effects of anodization process of aluminum oxide template fabrication on selective growth of Si nanowire arrays. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KA02	1.4	2
387	Formation of BaSi ₂ heterojunction solar cells using transparent MoO _x hole transport layers. <i>Applied Physics Letters</i> , 2015 , 106, 122104	3.4	15
386	Selective growth of vertical silicon nanowire array guided by anodic aluminum oxide template. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 095003	1.4	3
385	Absorption enhancement in nanotextured solar cells with Ge/Si heterostructures. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 04DR03	1.4	2
384	Structural and electrical characterizations of crack-free BaSi ₂ thin films fabricated by thermal evaporation. <i>Thin Solid Films</i> , 2015 , 595, 68-72	2.2	27
383	Application of heterojunction to Si-based solar cells using photonic nanostructures coupled with vertically aligned Ge quantum dots. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KA06	1.4	
382	Control of surface dip diameter in Si-based photonic nanostructures by changing growth temperature of Ge quantum dot multilayer structures and its impact on their optical properties. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KA01	1.4	4
381	Seed manipulation for artificially controlled defect technique in new growth method for quasi-monocrystalline Si ingot based on casting. <i>Applied Physics Express</i> , 2015 , 8, 105501	2.4	33
380	Comparison of phosphorus gettering effect in faceted dendrite and small grain of multicrystalline silicon wafers grown by floating cast method. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KD11	1.4	1
379	Influence of Substrate on Crystal Orientation of Large-Grained Si Thin Films Formed by Metal-Induced Crystallization. <i>International Journal of Photoenergy</i> , 2015 , 2015, 1-7	2.1	10
378	Relationship between dislocation density and contact angle of dendrite crystals in practical size silicon ingot. <i>Journal of Applied Physics</i> , 2015 , 117, 095701	2.5	10
377	Realization of single-phase BaSi ₂ films by vacuum evaporation with suitable optical properties and carrier lifetime for solar cell applications. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 07JE02	1.4	32
376	Fabrication of single-phase polycrystalline BaSi ₂ thin films on silicon substrates by vacuum evaporation for solar cell applications. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KC03	1.4	24
375	2015,		1
374	Enhanced photocarrier generation in large-scale photonic nanostructures fabricated from vertically aligned quantum dots. <i>Optics Express</i> , 2014 , 22 Suppl 2, A225-32	3.3	6
373	Potential variations around grain boundaries in impurity-doped BaSi ₂ epitaxial films evaluated by Kelvin probe force microscopy. <i>Journal of Applied Physics</i> , 2014 , 116, 123709	2.5	20
372	Influence of grain size and surface condition on minority-carrier lifetime in undoped n-BaSi ₂ on Si(111). <i>Journal of Applied Physics</i> , 2014 , 115, 193510	2.5	64
371	N-type doping of BaSi ₂ epitaxial films by arsenic ion implantation through a dose-dependent carrier generation mechanism. <i>Thin Solid Films</i> , 2014 , 567, 105-108	2.2	20

370	Enhanced Phosphorus Gettering of Impurities in Multicrystalline Silicon at Low Temperature. <i>Energy Procedia</i> , 2014 , 55, 203-210	2.3	8
369	Mono-Like Silicon Growth Using Functional Grain Boundaries to Limit Area of Multicrystalline Grains. <i>IEEE Journal of Photovoltaics</i> , 2014 , 4, 84-87	3.7	36
368	Orientation control of Ge thin films by underlayer-selected Al-induced crystallization. <i>CrystEngComm</i> , 2014 , 16, 2578	3.3	17
367	Precipitation control and activation enhancement in boron-doped p+-BaSi2 films grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2014 , 104, 252104	3.4	27
366	Analysis of the electrical properties of Cr/n-BaSi2 Schottky junction and n-BaSi2/p-Si heterojunction diodes for solar cell applications. <i>Journal of Applied Physics</i> , 2014 , 115, 223701	2.5	41
365	Evaluation of minority carrier diffusion length of undoped n-BaSi2 epitaxial thin films on Si(001) substrates by electron-beam-induced-current technique. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 078004	1.4	16
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36	Cathodoluminescence investigation of SiGe quantum wires fabricated on V-groove patterned Si substrates. <i>Journal of Crystal Growth</i> , 1995 , 150, 1070-1073	1.6	9
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34	Characterization of SiGe quantum wire structures by cathodoluminescence imaging and spectroscopy. <i>Applied Physics Letters</i> , 1995 , 67, 1709-1711	3.4	4
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31	Formation and Properties of SiGe/Si Quantum Wire Structures 1995 , 151-160		1
30	Optical Detection of Interdiffusion in Strained Si _{1-x} Gex/Si Quantum Well Structures. <i>Japanese Journal of Applied Physics</i> , 1994 , 33, 2344-2347	1.4	10
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27	Abrupt Si/Ge interface formation using atomic hydrogen in Si molecular beam epitaxy. <i>Applied Physics Letters</i> , 1994 , 65, 2975-2977	3.4	50
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23	A Si _{1-x} Ge _x /Si single quantum well p-i-n structure grown by solid-source and gas source Hybrid Si molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 1994 , 136, 355-360	1.6	1
22	Photoluminescence of Si/SiGe/Si quantum wells on separation by oxygen implantation substrate. <i>Applied Physics Letters</i> , 1994 , 64, 2373-2375	3.4	5
21	Self-modulating Sb incorporation in Si/SiGe superlattices during molecular beam epitaxial growth. <i>Surface Science</i> , 1993 , 295, 335-339	1.8	8
20	Dislocation glide motion in heteroepitaxial thin films of Si _{1-x} Ge _x /Si(100). <i>Philosophical Magazine Letters</i> , 1993 , 67, 165-171	1	41
19	Luminescence from Strained Si _{1-x} Ge _x /Si Quantum Wells Grown by Si Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1993 , 32, 1502-1507	1.4	35
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16	Band-edge photoluminescence of SiGe/strained-Si/SiGe type-II quantum wells on Si(100). <i>Applied Physics Letters</i> , 1993 , 63, 3509-3511	3.4	29
15	Luminescence study on interdiffusion in strained Si _{1-x} Ge _x /Si single quantum wells grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1993 , 63, 1651-1653	3.4	42
14	Realization of crescent-shaped SiGe quantum wire structures on a V-groove patterned Si substrate by gas-source Si molecular beam epitaxy. <i>Applied Physics Letters</i> , 1993 , 63, 2789-2791	3.4	45
13	High-temperature operation of strained Si _{0.65} Ge _{0.35} /Si(111) p-type multiple-quantum-well light-emitting diode grown by solid source Si molecular-beam epitaxy. <i>Applied Physics Letters</i> , 1993 , 63, 967-969	3.4	29
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10	Intense photoluminescence from strained Si _{1-x} Ge _x /Si quantum well structures. <i>Journal of Crystal Growth</i> , 1993 , 127, 489-493	1.6	3
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